

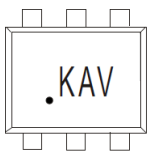
Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

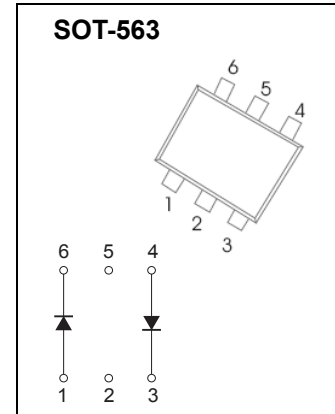
FEATURES

Surface mount schottky barrier diode arrays

Marking: KAV



Solid dot = Pin1 indicate.



Maximum Ratings @Ta=25°C

| Parameter | Symbol | Limit | Unit |
|---|---------------------------------|------------|------|
| Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 30 | V |
| Average Rectified Output Current | I_O | 200 | mA |
| Non-repetitive Peak Forward Surge Current @ t=8.3ms | I_{FSM} | 600 | mA |
| Repetitive Peak Forward Current @ t≤1s, δ ≤0.5 | I_{FRM} | 300 | mA |
| Power Dissipation | P_D | 150 | mW |
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | 667 | °C/W |
| Operating Junction Temperature Range | T_J | -40 ~ +125 | °C |
| Storage Temperature Range | T_{STG} | -55 ~ +125 | °C |

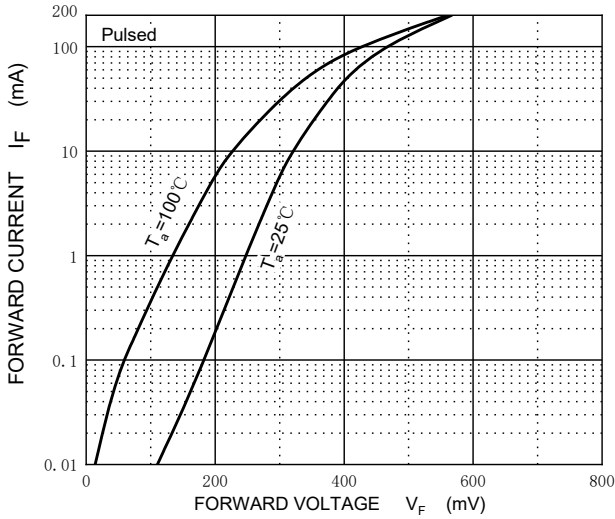
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Max | Unit |
|---------------------------------|------------|--|-----|---------------------------|------|
| Reverse breakdown voltage | $V_{(BR)}$ | $I_R=100\mu A$ | 30 | | V |
| Reverse voltage leakage current | I_R | $V_R=25V$ | | 2 | uA |
| Forward voltage | V_F | $I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$ | | 320 400 500 1000 | mV |
| Total capacitance | C_T | $V_R=1V, f=1MHz$ | | 15 | pF |
| Reverse recovery time | t_{rr} | $I_F=10mA, I_R=10mA\sim 1mA$ $R_L=100\Omega$ | | 5 | ns |

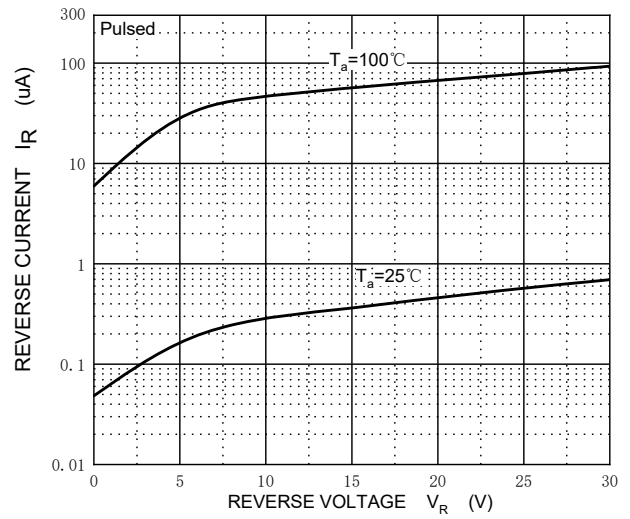


Typical Characteristics

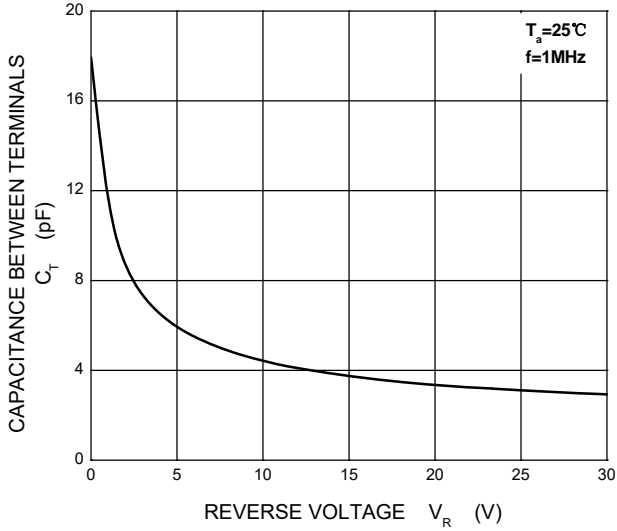
Forward Characteristics



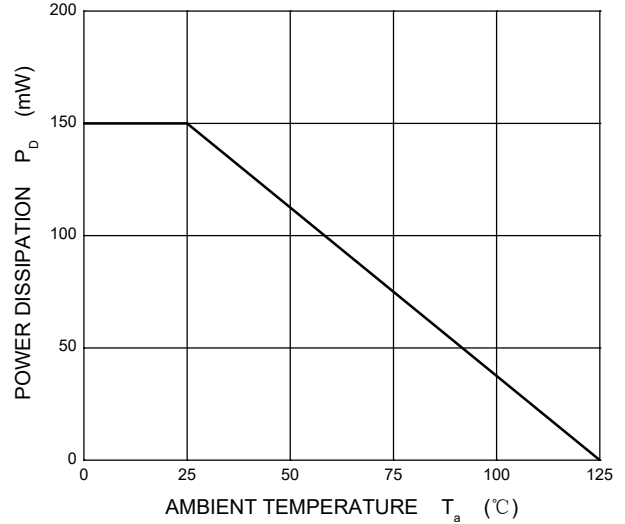
Reverse Characteristics



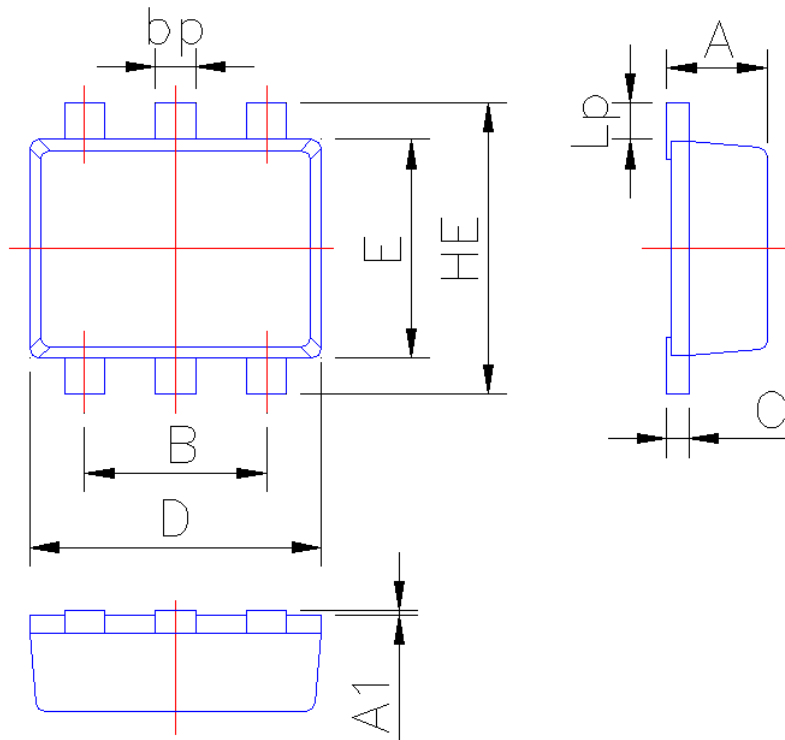
Capacitance Characteristics



Power Derating Curve



SOT-563-Package Outline Dimensions



| Symbol | Dimension in Millimeters | |
|--------|--------------------------|-------|
| | Min | Max |
| A | 0.50 | 0.60 |
| A1 | 0 | 0.05 |
| B | 0.95 | 1.05 |
| bp | 0.13 | 0.30 |
| C | 0.09 | 0.150 |
| D | 1.50 | 1.70 |
| E | 1.15 | 1.35 |
| HE | 1.40 | 1.80 |
| Lp | 0.13 | 0.30 |